In the Claims:

1. (Previously Presented) An electronic component comprising:

a wafer;

a plurality of bond pads disposed on a surface of the wafer;

a plurality of functional 3-D structures disposed on the surface of the wafer, such that each bond pad is laterally spaced from the plurality of bond pads so that each bond pad is associated with a laterally-spaced one of the 3-D structures, each functional 3-D structure including a non-conductive compliant base element and having an upper surface spaced from the surface of the wafer;

a plurality of reroute traces, each reroute trace extending over the surface of the wafer between a bond pad and its associated 3-D structure such that each reroute trace is electrically connected to one of the bond pads and extends onto the upper surface of the associated laterally-spaced one of the functional 3-D structures so that the reroute trace provides an electrical connection between the bond pad and the upper surface of the associated functional 3-D structure; and

a plurality of selected 3-D structures disposed on the surface of the wafer to provide a mechanical reinforcement, wherein at least some of the selected 3-D structures have a greater mechanical load-bearing capacity than some of the functional 3-D structures.

2. (Original) The component of claim 1 wherein each reroute trace comprises a copper/nickel layer that is covered by a gold layer.

3. (Original) The component of claim 1 wherein the selected 3-D structures have a lower degree of compressibility than the functional 3-D structures.

4. (Previously Presented) The component of claim 1 wherein the selected 3-D structures have a greater height than the functional 3-D structures.

5. (Previously Presented) The component of claim 1 wherein each of the selected 3-D structures includes a compliant base element that has a greater volume than the compliant base element of the functional 3-D structures.

6-7. (Cancelled)

8. (Original) The component of claim 1 wherein the selected 3-D structures are arranged in a regularly distributed manner in an edge region of the wafer.

9. (Original) The component of claim 1 wherein the selected 3-D structures are arranged in a regularly distributed manner over the wafer.

10. (Original) The component of claim 1 wherein the selected 3-D structures are able to be electrically bonded.

11-27. (Cancelled)

28. (Currently Amended) An electronic component comprising:

a wafer;

a plurality of bond pads disposed on the wafer;

a plurality of functional 3-D structures disposed on the wafer, each functional 3-D structure laterally spaced from an associated one of said plurality of bond pads including a compliant base element and having a first height;

a plurality of reroute traces, each reroute trace [[being]] extending from and electrically connected to one of the bond ~~pads and~~ pads, said reroute trace further extending onto a surface of one of the functional 3-D structures; and

a plurality of other 3-D structures disposed on the wafer to provide a mechanical reinforcement, each of the other 3-D structures having a second height that is greater than the first height.

29-30. (Cancelled)

31. (Previously Presented) The electronic component of claim 28 wherein the other 3-D structures have a lower degree of compressibility than the functional 3-D structures.

32. (Previously Presented) The electronic component of claim 28 wherein the other 3-D structures are arranged in a regularly distributed manner in an edge region of the wafer.

33. (Previously Presented) The electronic component of claim 28 wherein the other 3-D structures are arranged in a regularly distributed manner over the wafer.

34. (Previously Presented) The electronic component of claim 1, wherein the compliant base element is formed from silicone.